
BB101M

Build in Biasing Circuit MOS FET IC
UHF RF Amplifier

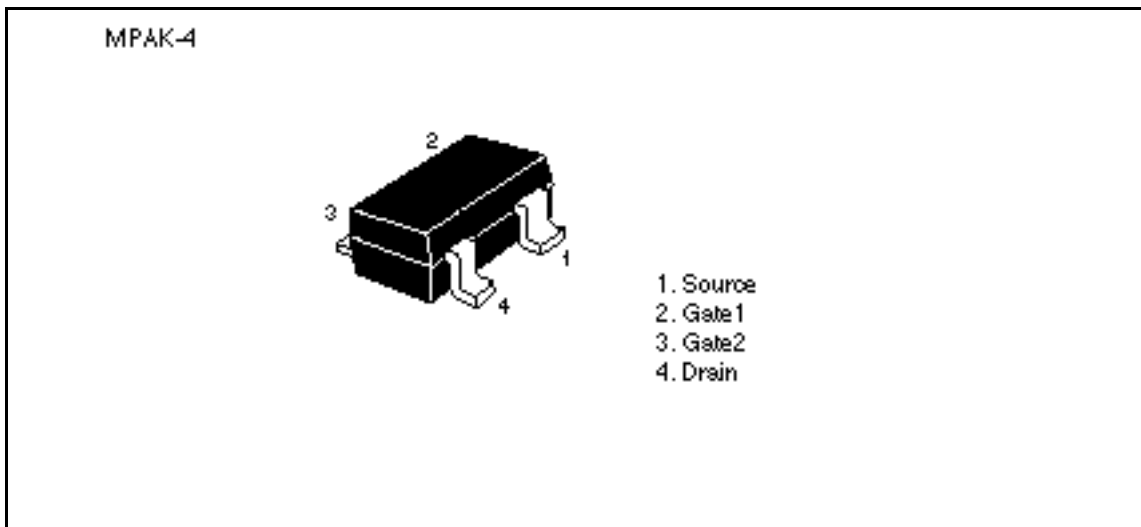
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ADE-208-504
1st. Edition

Features

- Build in Biasing Circuit; To reduce using parts cost & PC board space.
- Low noise characteristics; (NF = 2.0 dB typ. at f = 900 MHz)
- Withstanding to ESD; Build in ESD absorbing diode. Withstand up to 200 V at C = 200 pF, Rs = 0 conditions.

Outline



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Absolute Maximum Ratings (Ta = 25°C)

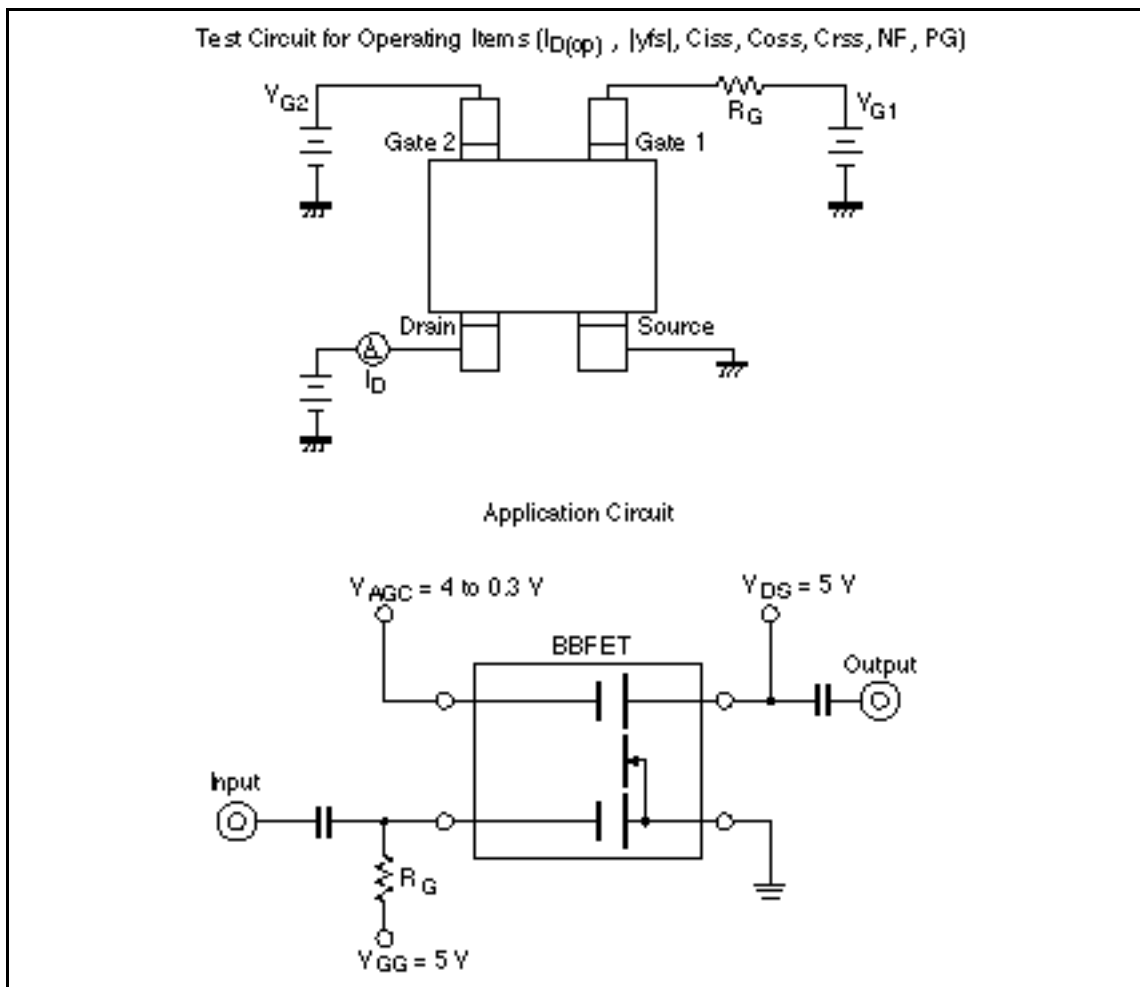
Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	6	V
Gate 1 to source voltage	V_{G1S}	+6 -0	V
Gate 2 to source voltage	V_{G2S}	±6	V
Drain current	I_D	25	mA
Channel power dissipation	Pch	150	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

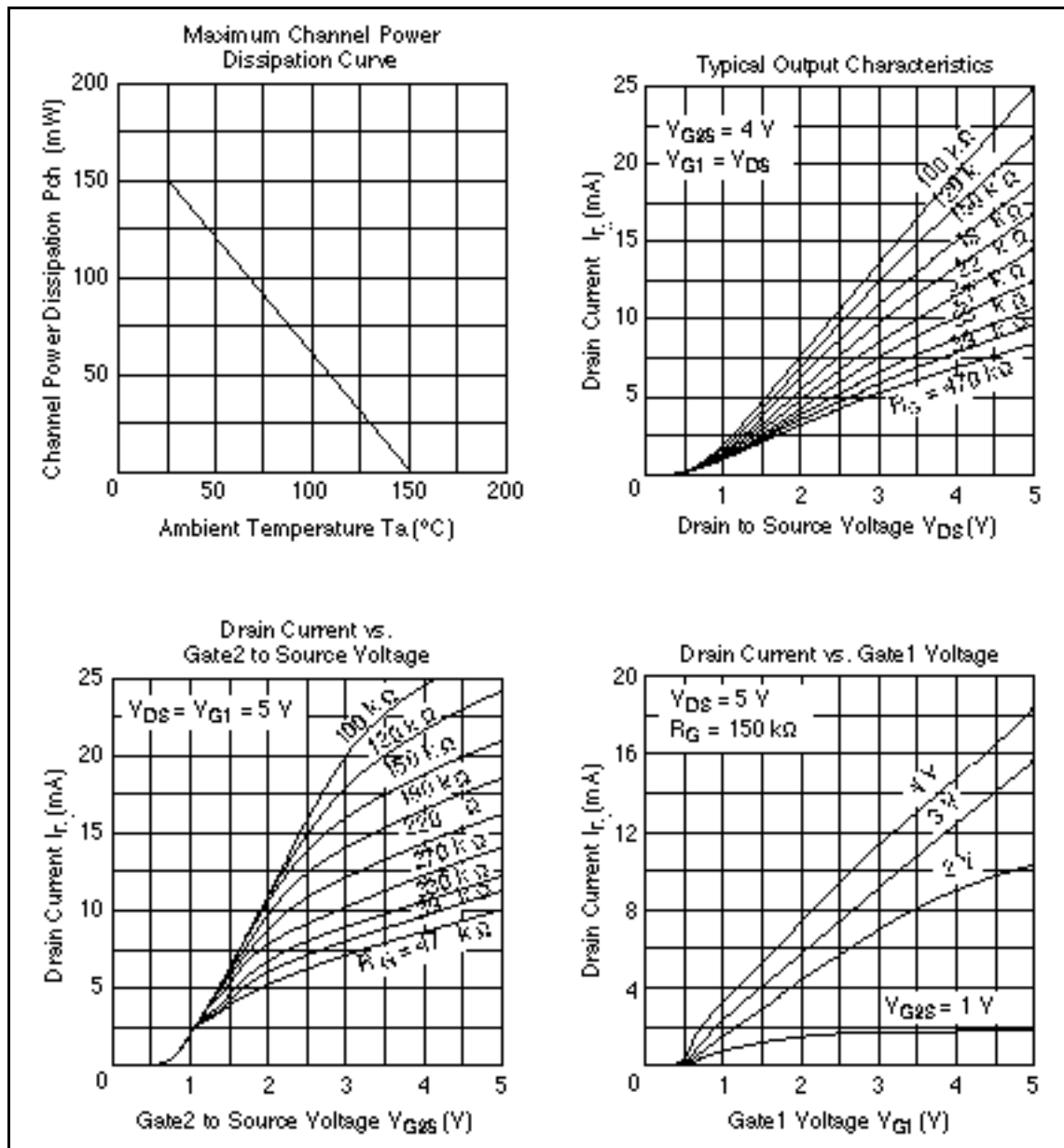
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	6	—	—	V	$I_D = 200 \mu A$ $V_{G1S} = V_{G2S} = 0$
Gate 1 to source breakdown voltage	$V_{(BR)G1SS}$	+6	—	—	V	$I_{G1} = +10 \mu A$ $V_{G2S} = V_{DS} = 0$
Gate 2 to source breakdown voltage	$V_{(BR)G2SS}$	±6	—	—	V	$I_{G2} = \pm 10 \mu A$ $V_{G1S} = V_{DS} = 0$
Gate 1 to source cutoff current	I_{G1SS}	—	—	+100	nA	$V_{G1S} = +5 V$ $V_{G2S} = V_{DS} = 0$
Gate 2 to source cutoff current	I_{G2SS}	—	—	±100	nA	$V_{G2S} = \pm 5 V$ $V_{G1S} = V_{DS} = 0$
Gate 1 to source cutoff voltage	$V_{G1S(off)}$	0.2	—	0.8	V	$V_{DS} = 5 V, V_{G2S} = 4 V$ $I_D = 100 \mu A$
Gate 2 to source cutoff voltage	$V_{G2S(off)}$	0.4	—	1.0	V	$V_{DS} = 5 V, V_{G1S} = 5 V$ $I_D = 100 \mu A$
Drain current	$I_{D(op)}$	10	15	20	mA	$V_{DS} = 5 V, V_{G1} = 5 V$ $V_{G2S} = 4 V, R_G = 220 k$
Forward transfer admittance	$ y_{fs} $	16	22	—	mS	$V_{DS} = 5 V, V_{G1} = 5 V,$ $V_{G2S} = 4 V,$ $R_G = 220 k, f = 1 kHz$
Input capacitance	Ciss	1.2	1.7	2.2	pF	$V_{DS} = 5 V, V_{G1} = 5 V$
Output capacitance	Coss	0.7	1.1	1.5	pF	$V_{G2S} = 4 V, R_G = 220 k$
Reverse transfer capacitance	Crss	—	0.012	0.03	pF	$f = 1 MHz$
Power gain	PG	16	20	—	dB	$V_{DS} = 5 V, V_{G1} = 5 V$ $V_{G2S} = 4 V$
Noise figure	NF	—	2.0	3.0	dB	$R_G = 220 k, f = 900 MHz$

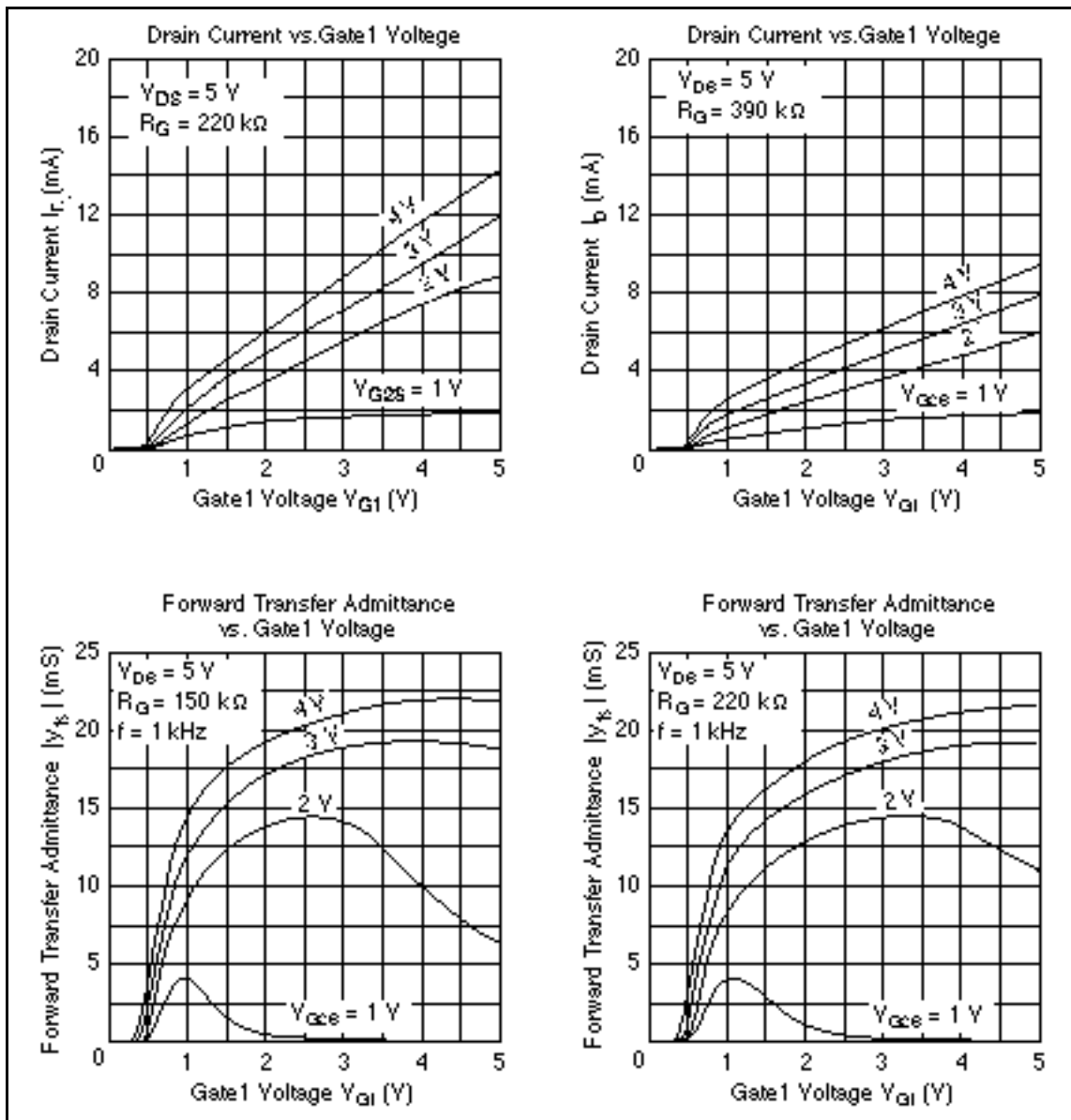
Note: Marking is "AU-".

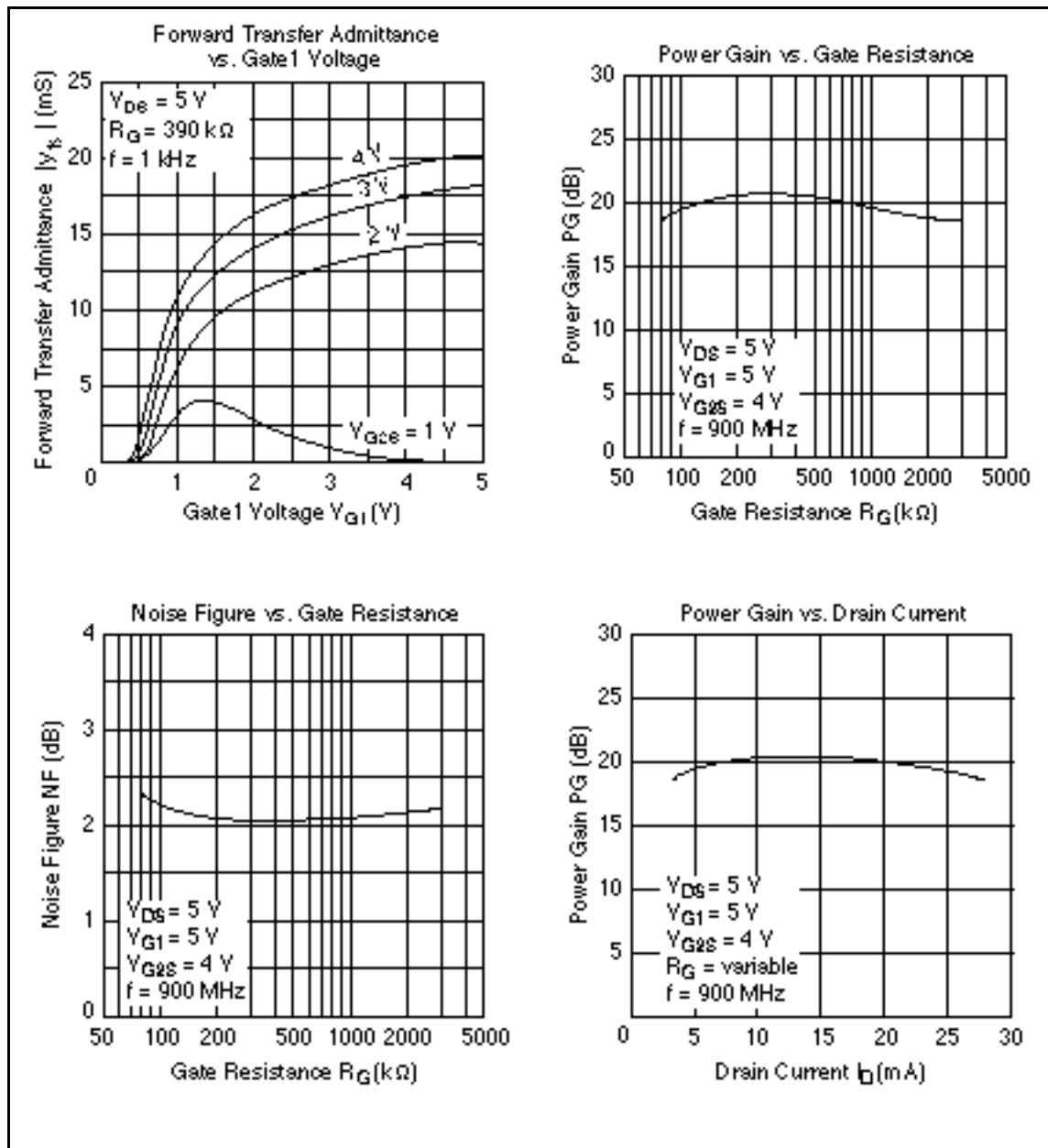
Main Characteristics

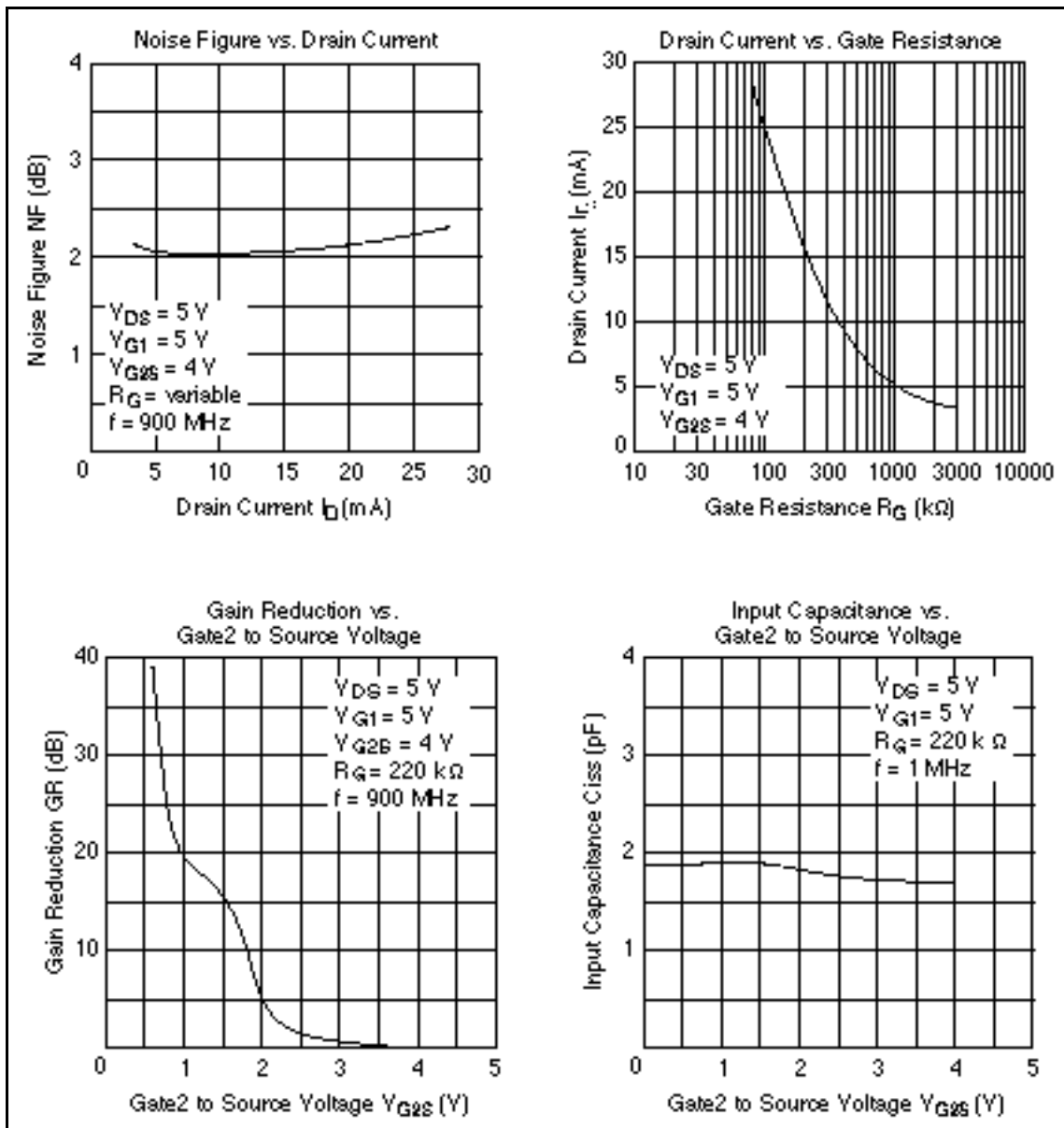


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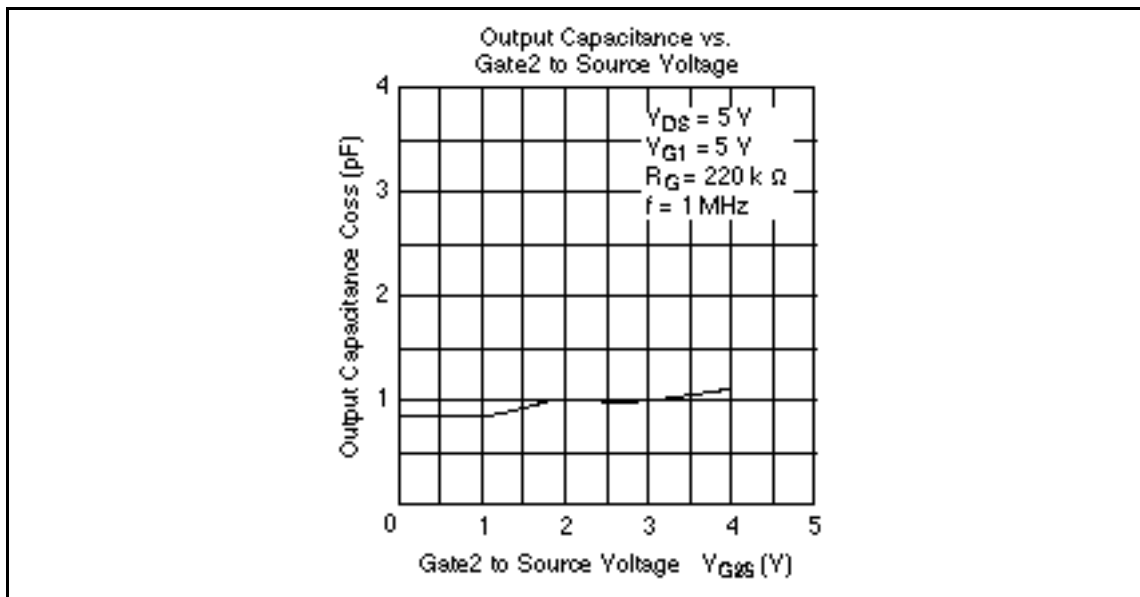








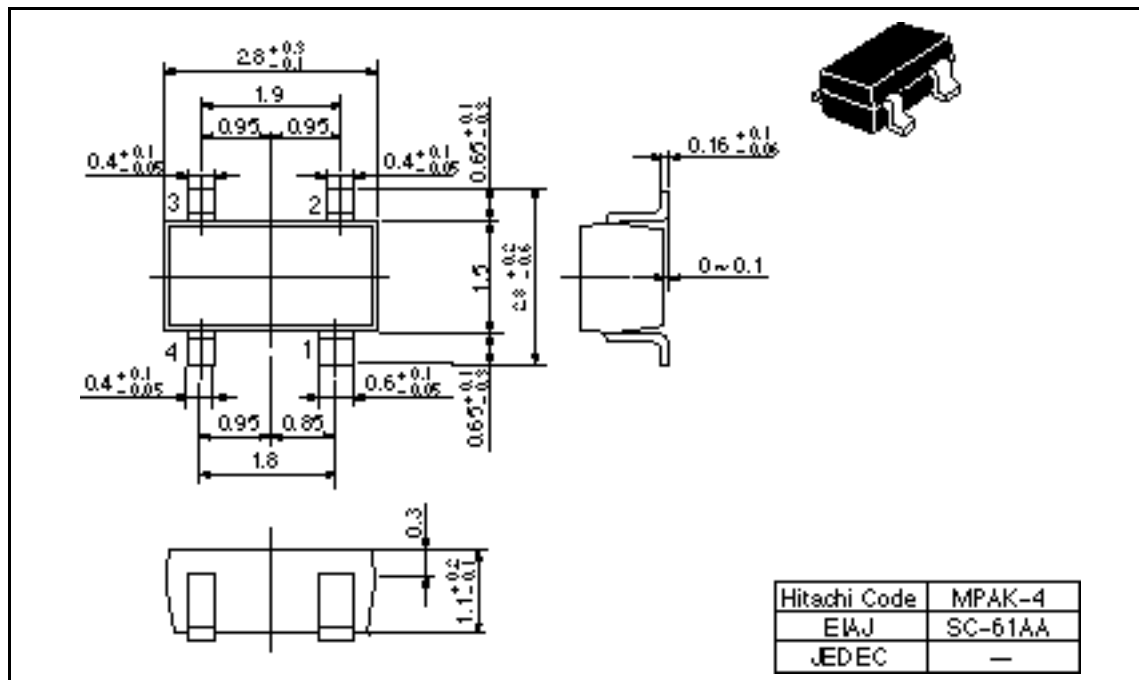
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Package Dimensions

Unit: mm



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Hitachi, Ltd.

Semiconductor & IC Div.

Nippon Bldg., 2-5-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan

Tel Tokyo (03) 3270-2111

Fax (03) 3270-5109

For further information write to:

Hitachi America, Ltd.

Semiconductor & IC Div.

2000 Sierra Point Parkway

Folsom, CA 94005-4835

U.S.A.

Tel 415-589-8300

Fax 415-589-4207

Hitachi Europe GmbH

Electronic Components Group

Continental Europe

Darnecker Straße 3

D-85622 Feldkirchen

München

Tel 089-9 91 80-0

Fax 089-9 29 30 00

Hitachi Europe Ltd.

Electronic Components Div.

Northern Europe Headquarters

Whitebrook Park

Lower Cookham Road

High Wycombe

Berkshire SL6 6YA

United Kingdom

Tel 0628-885000

Fax 0628-778322

Hitachi Asia Pte. Ltd.

45 Collyer Quay #20-00

Hitachi Tower

Singapore 0104

Tel 535-2100

Fax 535-1533

Hitachi Asia (Hong Kong) Ltd.

Unit 705, North Tower,

World Finance Centre

Harbour City, Canton Road

Tsim Sha Tsui, Kowloon

Hong Kong

Tel 27359218

Fax 27308074

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